5-Line Transient Voltage Suppressor Array

NUP8020X6

This 5−line voltage transient suppressor array is designed for application requiring transient voltage protection capability. It is intended for use in over−transient voltage and ESD sensitive equipment such as cell phones, portables, computers, printers and other applications. This device features a monolithic common anode design which protects five independent lines in a single SOT−563 package.

Features

- Protects up to 5 Lines in a Single SOT−563 Package
- ESD Rating of Class 3B (Exceeding 8 kV) per Human Body Model and Class C (Exceeding 400 V) per Machine Model.
- Compliance with IEC 61000−4−2 (ESD) 15 kV (Air), 8 kV (Contact)
- This is a Pb−Free Device

Applications

- Hand Held Portable Applications
- Serial and Parallel Ports
- Notebooks, Desktops, Servers

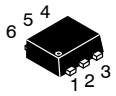
MAXIMUM RATINGS (T_J = 25°C, unless otherwise specified)

Symbol	Rating	Value	Unit
P_{PK} 1	Peak Power Dissipation 8x20 μsec double exponential waveform, (Note 1)	90	W
T_J	Operating Junction Temperature Range	−40 to 125	°C
T_{STG}	Storage Temperature Range	−55 to 150	°C
T_L	Lead Solder Temperature − Maximum (10 seconds)	260	°C
ESD	Human Body Model (HBM) Machine Model (MM) IEC 61000−4−2 Air (ESD) IEC 61000−4−2 Contact (ESD)	16000 400 15000 8000	V

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

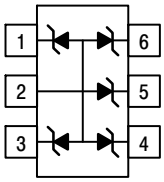
1. Non−repetitive current pulse per Figure 1.

SOT−563 5−LINE TRANSIENT VOLTAGE SUPPRESSOR



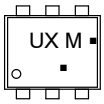
SOT−563
CASE 463A
STYLE 6

PIN ASSIGNMENT



PIN 1. CATHODE
2. ANODE
3. CATHODE
4. CATHODE
5. CATHODE
6. CATHODE

MARKING DIAGRAM



UX = Specific Device Code
M = Month Code
▪ = Pb−Free Package

(Note: Microdot may be in either location)

ORDERING INFORMATION

Device	Package	Shipping†
NUP8020X6T1G	SOT−563 (Pb−Free)	4,000/Tape & Reel

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specification Brochure, BRD8011/D.

ELECTRICAL CHARACTERISTICS (T_J = 25°C, unless otherwise specified)

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
V_{RWM}	Reverse Working Voltage	(Note 2)		−	5.0	V
V_{BR}	Breakdown Voltage	I_T = 1 mA, (Note 3)	6.2	6.8	7.2	V
I_R	Reverse Leakage Current	V_{RWM} = 3 V	−	0.01	0.5	μA
C_J	Capacitance	V_R = 0 V, f = 1 MHz (Line to GND) V_R = 2.5 V, f = 1 MHz (Line to GND)	−	54	70	pF

2. TVS devices are normally selected according to the working peak reverse voltage (V_{RWM}), which should be equal or greater than the DC or continuous peak operating voltage level.
3. V_{BR} is measured at pulse test current I_T.

TYPICAL CHARACTERISTICS

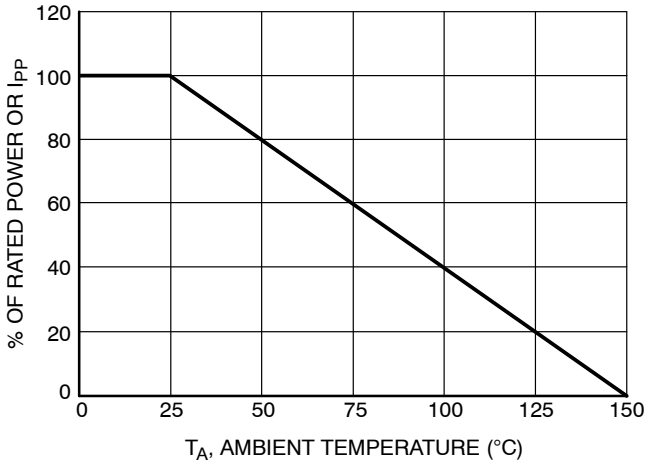


Figure 1. Power Derating vs. Ambient Temperature

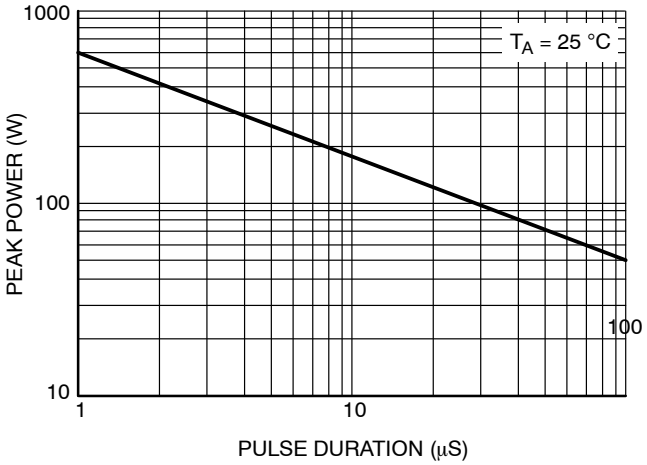


Figure 2. Peak Power vs. Pulse Duration

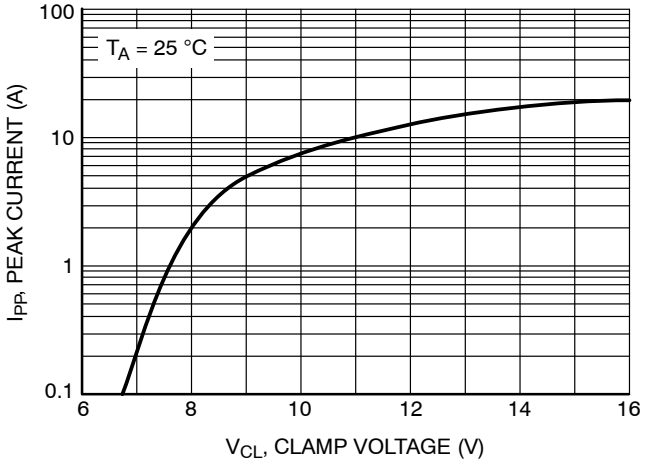


Figure 3. Peak Current vs. Clamp Voltage

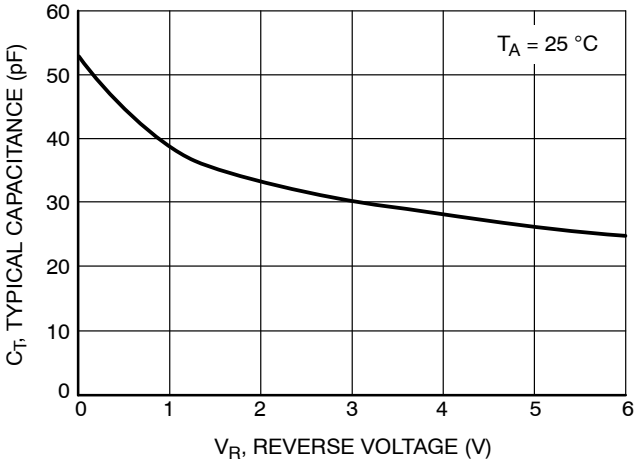


Figure 4. Typical Capacitance vs. Reverse Voltage

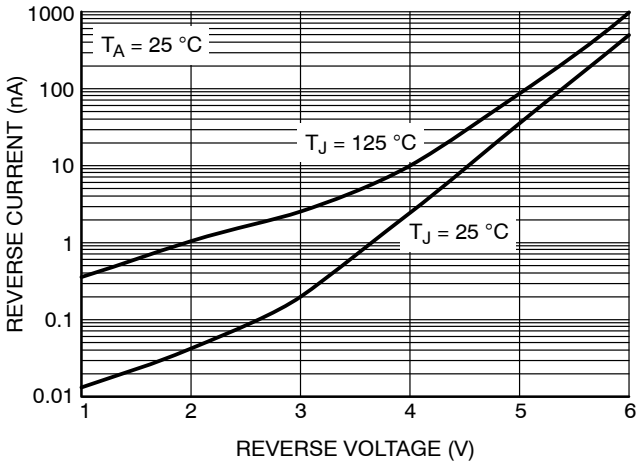


Figure 5. Reverse Current vs. Reverse Voltage

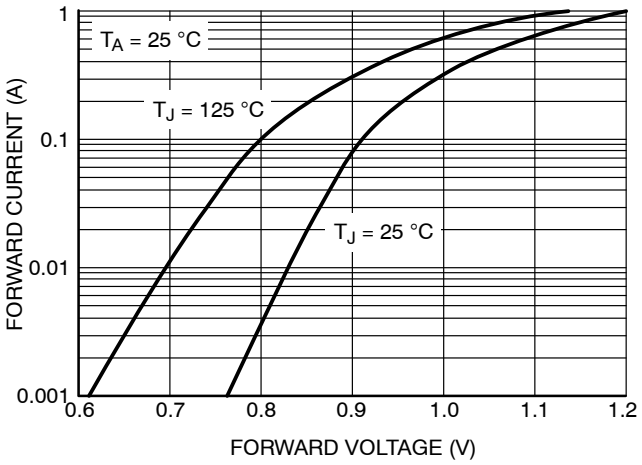
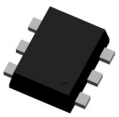


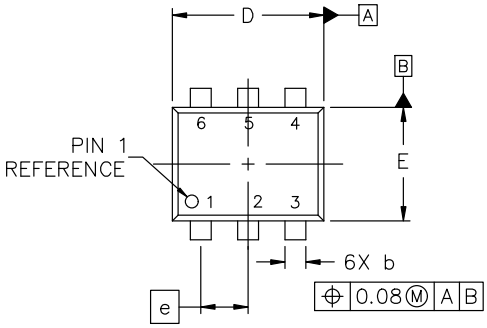
Figure 6. Typical Forward Current vs. Forward Voltage



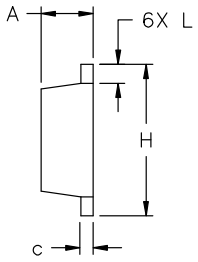
SOT−563−6 1.60x1.20x0.55, 0.50P
CASE 463A
ISSUE J

DATE 15 FEB 2024

NOTES:
1. DIMENSIONING AND TOLERANCING CONFORM TO ASME Y14.5−2018.
2. ALL DIMENSION ARE IN MILLIMETERS.
3. MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH THICKNESS. MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF BASE MATERIAL.

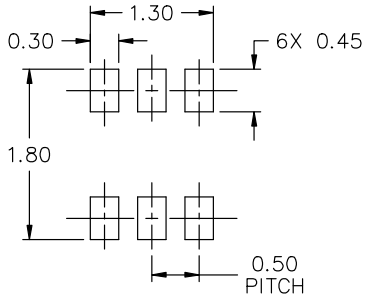


TOP VIEW



SIDE VIEW

DIM	MILLIMETERS		
	MIN.	NOM.	MAX.
A	0.50	0.55	0.60
b	0.17	0.22	0.27
c	0.08	0.13	0.18
D	1.50	1.60	1.70
E	1.10	1.20	1.30
e	0.50 BSC		
H	1.50	1.60	1.70
L	0.10	0.20	0.30



RECOMMENDED MOUNTING FOOTPRINT*

* FOR ADDITIONAL INFORMATION ON OUR Pb−FREE STRATEGY AND SOLDERING DETAILS, PLEASE DOWNLOAD THE ON SEMICONDUCTOR SOLDERING AND MOUNTING TECHNIQUES REFERENCE MANUAL, SOLDERRM/D.

STYLE 1:
PIN 1. EMITTER 1
2. BASE 1
3. COLLECTOR 2
4. EMITTER 2
5. BASE 2
6. COLLECTOR 1

STYLE 2:
PIN 1. EMITTER 1
2. EMITTER 2
3. BASE 2
4. COLLECTOR 2
5. BASE 1
6. COLLECTOR 1

STYLE 3:
PIN 1. CATHODE 1
2. CATHODE 1
3. ANODE/ANODE 2
4. CATHODE 2
5. CATHODE 2
6. ANODE/ANODE 1

STYLE 4:
PIN 1. COLLECTOR
2. COLLECTOR
3. BASE
4. EMITTER
5. COLLECTOR
6. COLLECTOR

STYLE 5:
PIN 1. CATHODE
2. CATHODE
3. ANODE
4. ANODE
5. CATHODE
6. CATHODE

STYLE 6:
PIN 1. CATHODE
2. ANODE
3. CATHODE
4. CATHODE
5. CATHODE
6. CATHODE

STYLE 7:
PIN 1. CATHODE
2. ANODE
3. CATHODE
4. CATHODE
5. ANODE
6. CATHODE

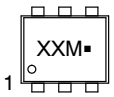
STYLE 8:
PIN 1. DRAIN
2. DRAIN
3. GATE
4. SOURCE
5. DRAIN
6. DRAIN

STYLE 9:
PIN 1. SOURCE 1
2. GATE 1
3. DRAIN 2
4. SOURCE 2
5. GATE 2
6. DRAIN 1

STYLE 10:
PIN 1. CATHODE 1
2. N/C
3. CATHODE 2
4. ANODE 2
5. N/C
6. ANODE 1

STYLE 11:
PIN 1. EMITTER 2
2. BASE 2
3. COLLECTOR 1
4. EMITTER 1
5. BASE 1
6. COLLECTOR 2

GENERIC MARKING DIAGRAM*



XX = Specific Device Code
M = Month Code
▪ = Pb−Free Package

*This information is generic. Please refer to device data sheet for actual part marking. Pb−Free indicator, “G” or microdot “▪”, may or may not be present. Some products may not follow the Generic Marking.

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DESCRIPTION:	**SOT−563−6 1.60x1.20x0.55, 0.50P**		**PAGE 1 OF 1**

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